

Abstract of the Disclosure

A silicon single crystal prepared by the Czochralski method including a neck having an upper portion, an intermediate portion, and a lower portion.

- 5 The upper portion contains dislocations. The intermediate portion is between the upper and lower portions. A majority of the intermediate and lower portions has a diameter greater than 10 millimeters, and the lower portion is free of dislocations. The crystal
- 10 also includes an outwardly flaring segment adjacent the lower portion of the neck, and a body adjacent the outwardly flaring segment.

This Sheet Has Been Replaced

